

FQA36P15

P-Channel QFET® MOSFET

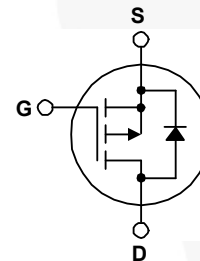
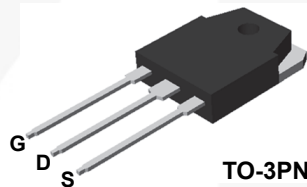
-150 V, -36 A, 90 mΩ

Features

- -36 A, -150 V, $R_{DS(on)} = 90 \text{ m}\Omega$ (Max) @ $V_{GS} = -10 \text{ V}$, $I_D = -18 \text{ A}$
- Low Gate Charge (Typ. 81 nC)
- Low Crss (Typ. 110 pF)
- 100% Avalanche Tested
- 175°C Maximum Junction Temperature Rating

Description

This P-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.



Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

| Symbol | Parameter | FQA36P15 | Unit |
|-----------------------------------|---|-------------|------|
| V _{DSS} | Drain-Source Voltage | -150 | V |
| I _D | Drain Current - Continuous (T _C = 25°C) | -36 | A |
| | Drain Current - Continuous (T _C = 100°C) | -25.5 | A |
| I _{DM} | Drain Current - Pulsed (Note 1) | -144 | A |
| V _{GSS} | Gate-Source Voltage | ± 30 | V |
| E _{AS} | Single Pulsed Avalanche Energy (Note 2) | 1400 | mJ |
| I _{AR} | Avalanche Current (Note 1) | -36 | A |
| E _{AR} | Repetitive Avalanche Energy (Note 1) | 29.4 | mJ |
| dv/dt | Peak Diode Recovery dv/dt (Note 3) | -5.0 | V/ns |
| P _D | Power Dissipation (T _C = 25°C) | 294 | W |
| | - Derate above 25°C | 1.96 | W/°C |
| T _J , T _{STG} | Operating and Storage Temperature Range | -55 to +175 | °C |
| T _L | Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds | 300 | °C |

Thermal Characteristics

| Symbol | Parameter | FQA36P15 | Unit |
|------------------|---|----------|------|
| R _{θJC} | Thermal Resistance, Junction-to-Case, Max. | 0.51 | °C/W |
| R _{θCS} | Thermal Resistance, Case-to-Sink, Typ. | 0.24 | °C/W |
| R _{θJA} | Thermal Resistance, Junction-to-Ambient, Max. | 40 | °C/W |

Package Marking and Ordering Information

| Part Number | Top Mark | Package | Packing Method | Reel Size | Tape Width | Quantity |
|-------------|----------|---------|----------------|-----------|------------|----------|
| FQA36P15 | FQA36P15 | TO-3PN | Tube | N/A | N/A | 30 units |

Electrical Characteristics T_C = 25°C unless otherwise noted.

| Symbol | Parameter | Test Conditions | Min | Typ | Max | Unit | |
|---|---|---|----------|-------|------|------|----|
| Off Characteristics | | | | | | | |
| BV _{DSS} | Drain-Source Breakdown Voltage | V _{GS} = 0 V, I _D = -250 μA | -150 | -- | -- | V | |
| ΔBV _{DSS} /ΔT _J | Breakdown Voltage Temperature Coefficient | I _D = -250 μA, Referenced to 25°C | -- | -0.13 | -- | V/°C | |
| I _{DSS} | Zero Gate Voltage Drain Current | V _{DS} = -150 V, V _{GS} = 0 V | -- | -- | -10 | μA | |
| | | V _{DS} = -120 V, T _C = 150°C | -- | -- | -100 | μA | |
| I _{GSSF} | Gate-Body Leakage Current, Forward | V _{GS} = -25 V, V _{DS} = 0 V | -- | -- | -100 | nA | |
| I _{GSSR} | Gate-Body Leakage Current, Reverse | V _{GS} = 25 V, V _{DS} = 0 V | -- | -- | 100 | nA | |
| On Characteristics | | | | | | | |
| V _{GS(th)} | Gate Threshold Voltage | V _{DS} = V _{GS} , I _D = -250 μA | -2.0 | -- | -4.0 | V | |
| R _{DS(on)} | Static Drain-Source On-Resistance | V _{GS} = -10 V, I _D = -18 A | -- | 0.076 | 0.09 | Ω | |
| g _{FS} | Forward Transconductance | V _{DS} = -40 V, I _D = -18 A | -- | 19.5 | -- | S | |
| Dynamic Characteristics | | | | | | | |
| C _{iss} | Input Capacitance | V _{DS} = -25 V, V _{GS} = 0 V, f = 1.0 MHz | -- | 2550 | 3320 | pF | |
| C _{oss} | Output Capacitance | | -- | 710 | 920 | pF | |
| C _{rss} | Reverse Transfer Capacitance | | -- | 110 | 140 | pF | |
| Switching Characteristics | | | | | | | |
| t _{d(on)} | Turn-On Delay Time | V _{DD} = -75 V, I _D = -36 A, R _G = 25 Ω | -- | 50 | 110 | ns | |
| t _r | Turn-On Rise Time | | -- | 350 | 710 | ns | |
| t _{d(off)} | Turn-Off Delay Time | | (Note 4) | -- | 155 | 320 | ns |
| t _f | Turn-Off Fall Time | | (Note 4) | -- | 150 | 310 | ns |
| Q _g | Total Gate Charge | V _{DS} = -120 V, I _D = -36 A, V _{GS} = -10 V | -- | 81 | 105 | nC | |
| Q _{gs} | Gate-Source Charge | | (Note 4) | -- | 19 | -- | nC |
| Q _{gd} | Gate-Drain Charge | | (Note 4) | -- | 42 | -- | nC |
| Drain-Source Diode Characteristics and Maximum Ratings | | | | | | | |
| I _S | Maximum Continuous Drain-Source Diode Forward Current | | -- | -- | -36 | A | |
| I _{SM} | Maximum Pulsed Drain-Source Diode Forward Current | | -- | -- | -144 | A | |
| V _{SD} | Drain-Source Diode Forward Voltage | V _{GS} = 0 V, I _S = -36 A | -- | -- | -4.0 | V | |
| t _{rr} | Reverse Recovery Time | V _{GS} = 0 V, I _S = -36 A, dI _F / dt = 100 A/μs | -- | 198 | -- | ns | |
| Q _{rr} | Reverse Recovery Charge | | -- | 1.45 | -- | μC | |

Notes:

1. Repetitive rating: pulse-width limited by maximum junction temperature.
2. L = 1.45 mH, I_{AS} = -36 A, V_{DD} = -50 V, R_G = 25 Ω, starting T_J = 25°C.
3. I_{SD} ≤ -36 A, di/dt ≤ 300 A/μs, V_{DD} ≤ BV_{DSS}, starting T_J = 25°C.
4. Essentially independent of operating temperature typical characteristics.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

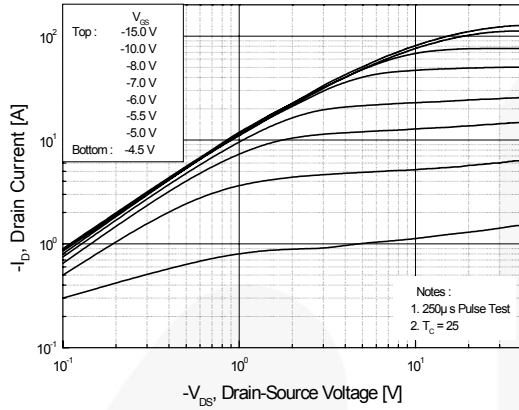


Figure 2. Transfer Characteristics

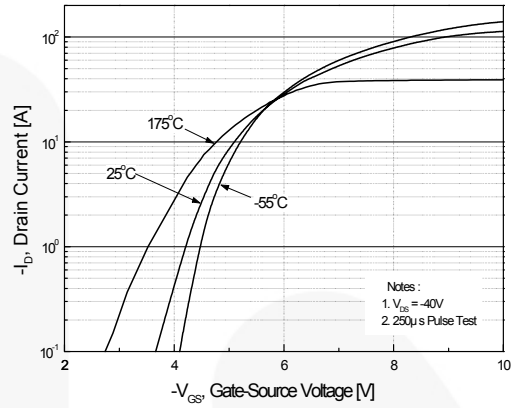


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

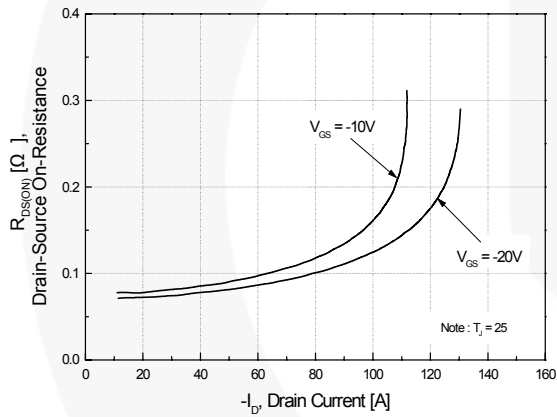


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

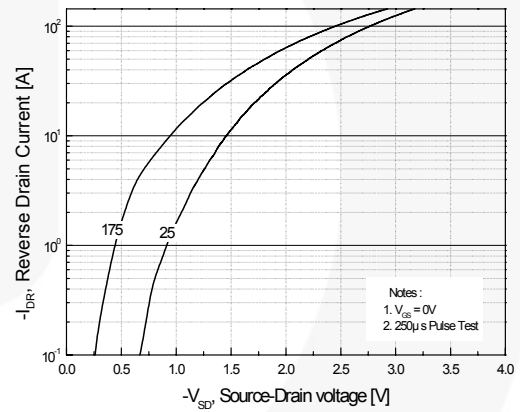


Figure 5. Capacitance Characteristics

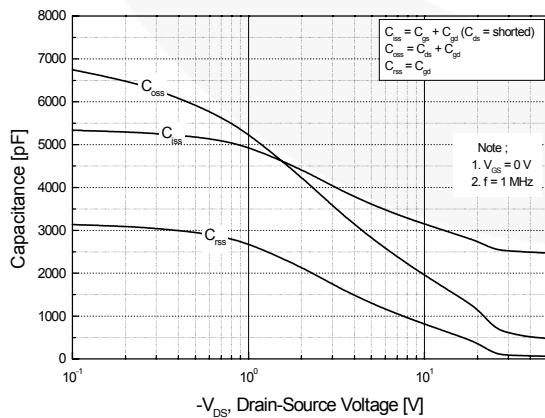
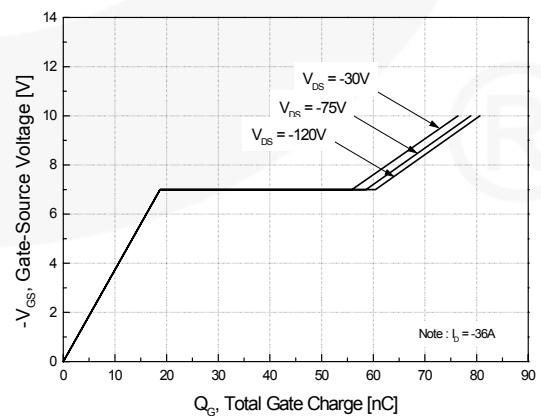


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

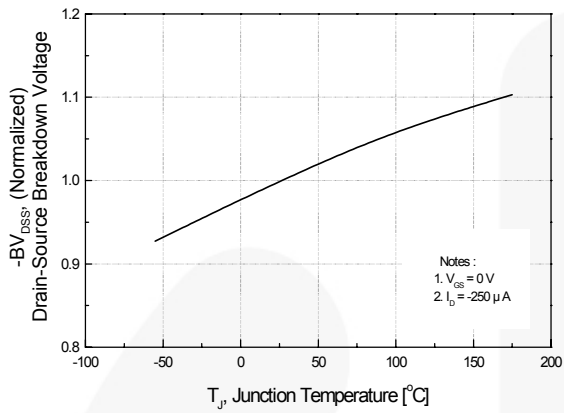


Figure 8. On-Resistance Variation vs. Temperature

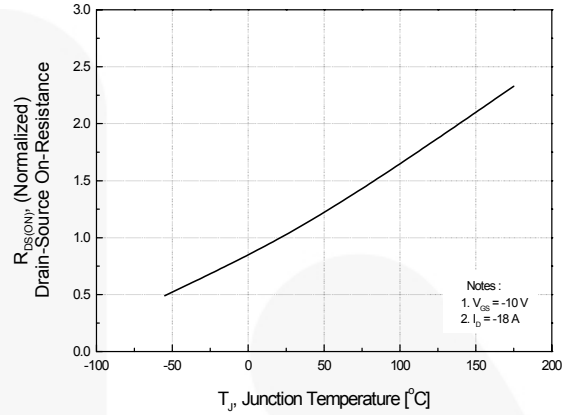


Figure 9. Maximum Safe Operating Area

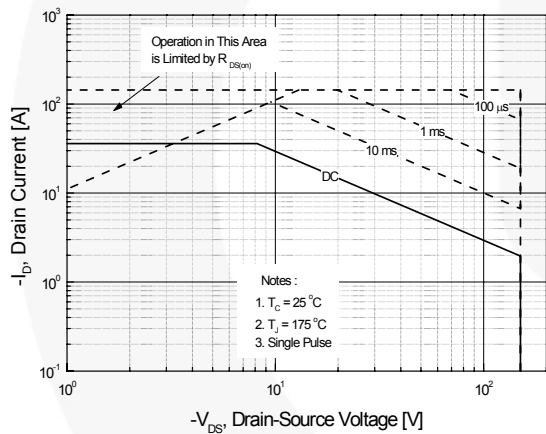


Figure 10. Maximum Drain Current vs. Case Temperature

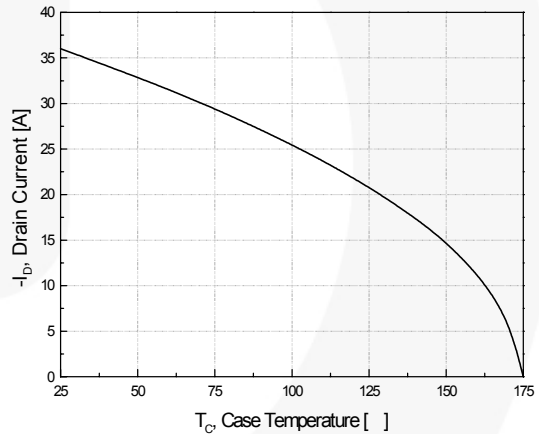
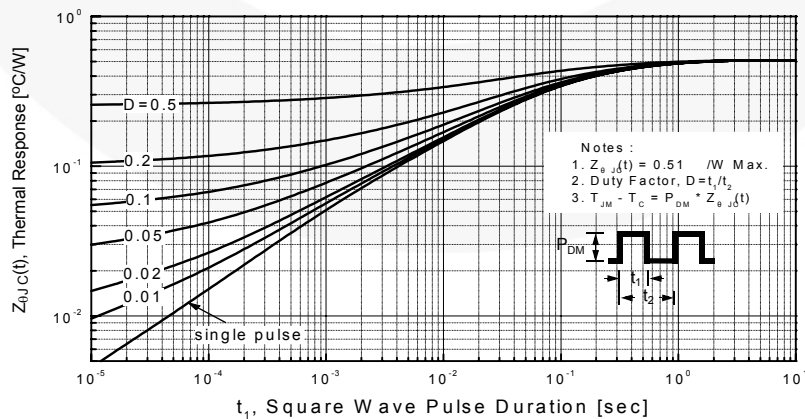


Figure 11. Transient Thermal Response Curve



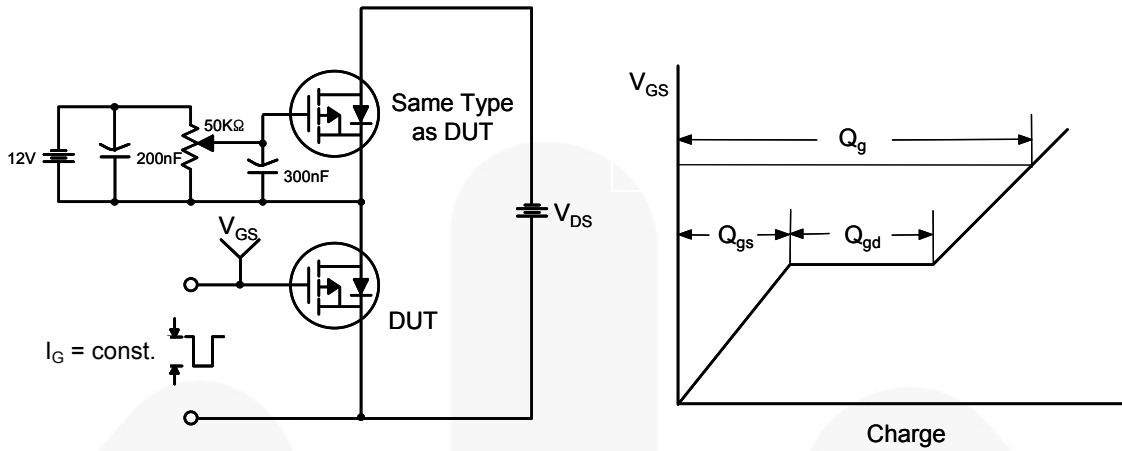


Figure 12. Gate Charge Test Circuit & Waveform

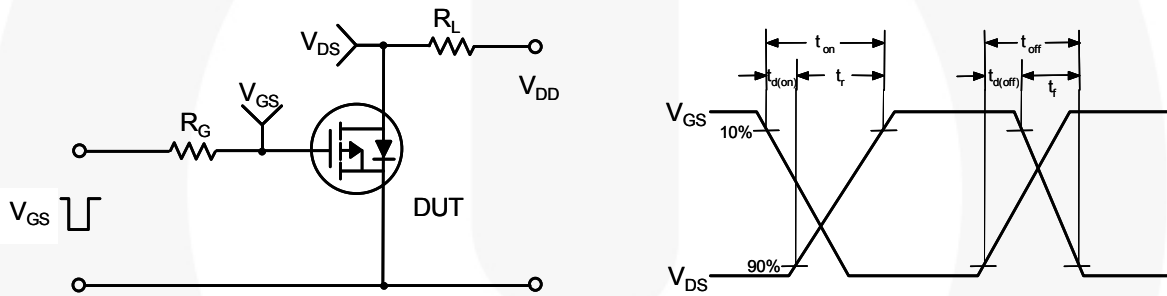


Figure 13. Resistive Switching Test Circuit & Waveforms

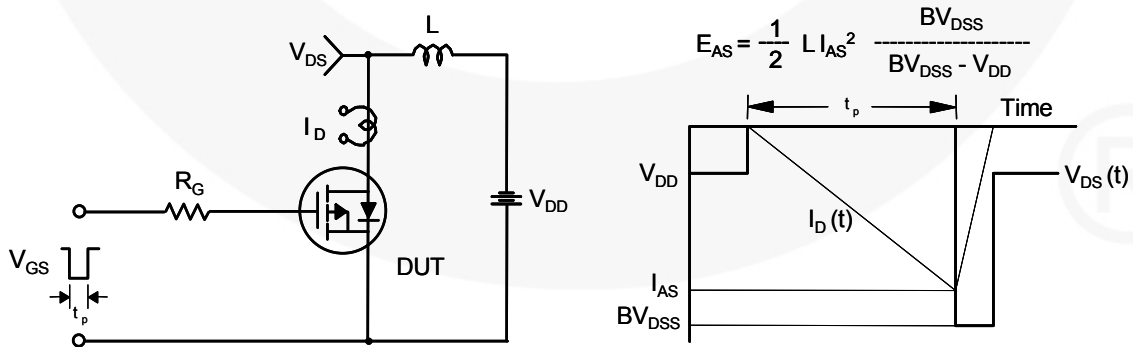


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

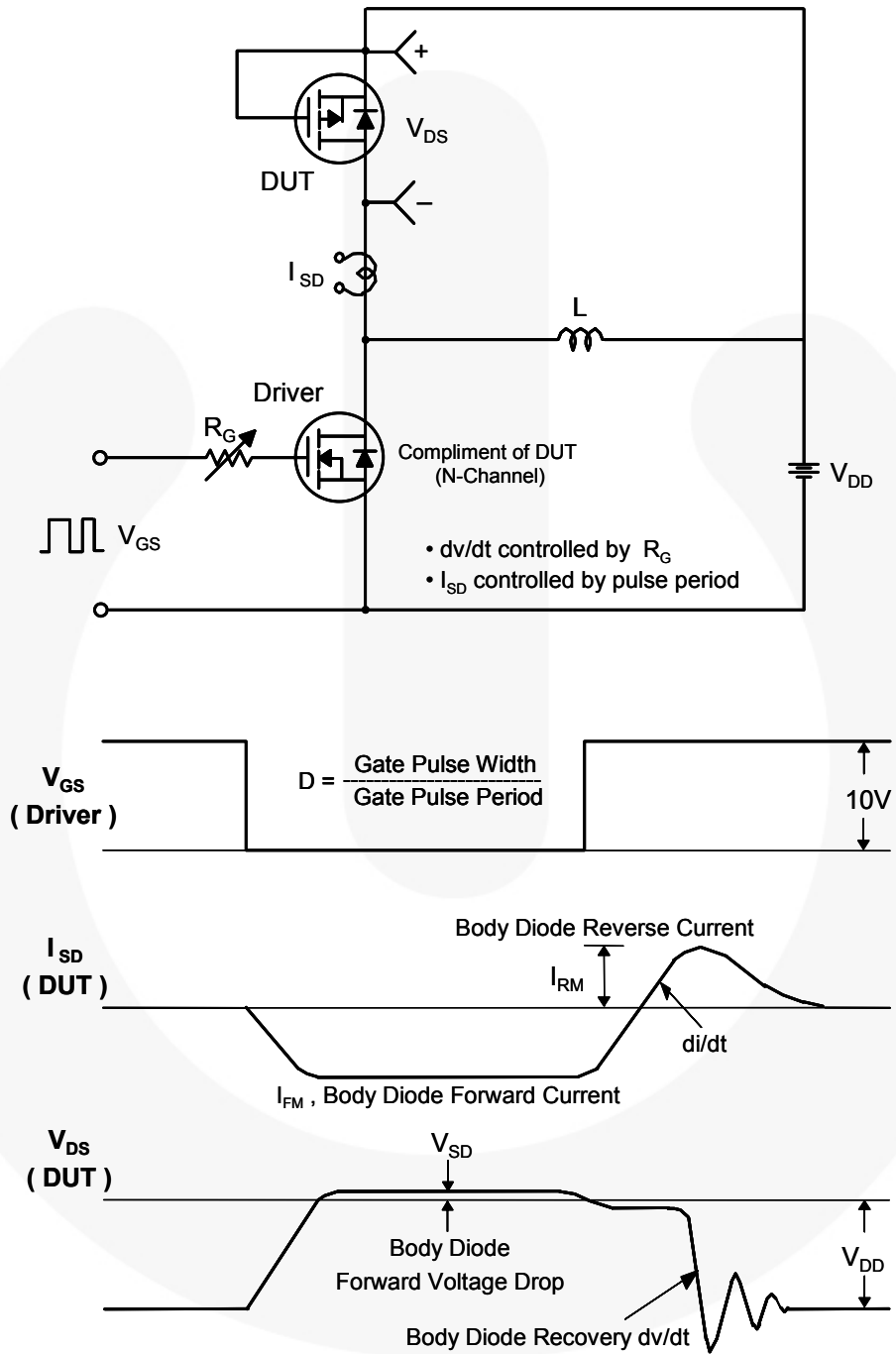
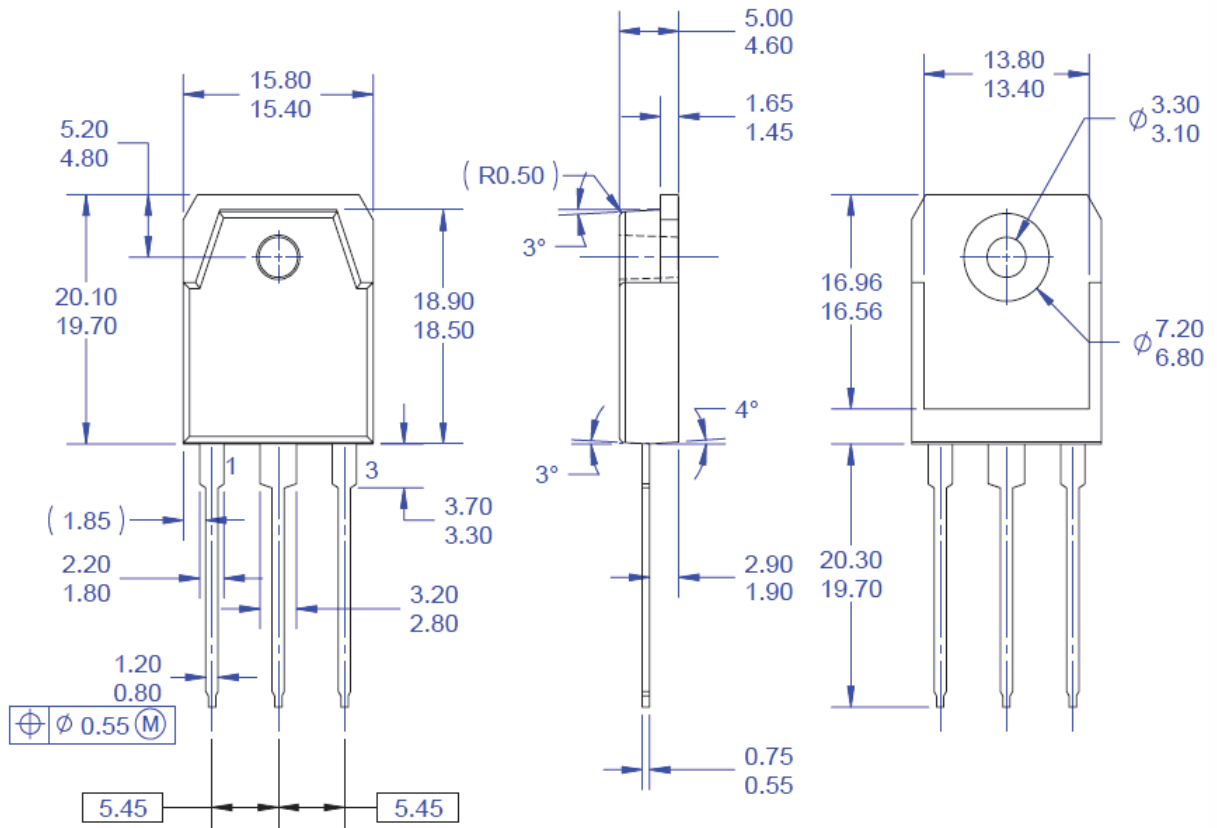


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions



NOTES: UNLESS OTHERWISE SPECIFIED

- THIS PACKAGE CONFORMS TO EIAJ SC-65 PACKAGING STANDARD.
- ALL DIMENSIONS ARE IN MILLIMETERS.
- DIMENSION AND TOLERANCING PER ASME14.5
- DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
- THIS PACKAGE IS INTENDED ONLY FOR TO3PN.
- DRAWING FILE NAME: TO3P03AREV4.



Figure 16. TO3, 3-Lead, Plastic, EIAJ SC-65

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